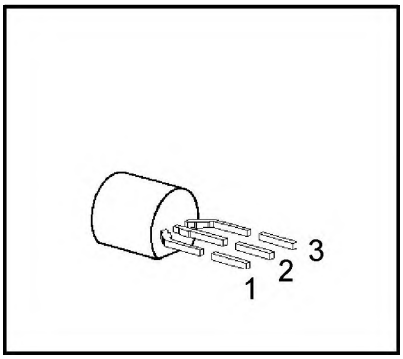
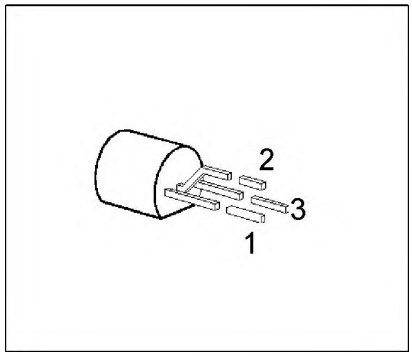
SIEMENS

SIPMOS® Small-Signal Transistor — BSS 110

- V_{DS} – 50 V
- I_D – 0.17 A
- $R_{DS(on)}$ 10 Ω
- $V_{GS(th)}$ – 0.8 … – 2.0 V
- P channel
- Enhancement mode
- Logic level





Type	Ordering Code	Tape and Reel Information	Pin Configuration 1	2	3	Marking	Package
BSS 110	Q62702-S489	bulk	S	G	D	BSS 110 marked SS110	TO-92
BSS 110	Q62702-S500	E6288: 1500 pcs/reel; 2 reels/carton; gate first					
BSS 110	Q67000-S278	E6296: 1500 pcs/reel; 2 reels/carton; source first					
BSS 110	Q62702-S658	E6325: 2000 pcs/carton; Ammopack					

Maximum Ratings

Parameter	Symbol	Values	Unit
Drain-source voltage	V_{DS}	– 50	V
Drain-gate voltage, R_{GS} = 20 kΩ	V_{DGR}	– 50	
Gate-source voltage	V_{GS}	± 20	
Continuous drain current, T_A = 35 ℃	I_D	– 0.17	A
Pulsed drain current, T_A = 25 ℃	$I_{D\,puls}$	– 0.68	
Max. power dissipation, T_A = 25 ℃	P_{tot}	0.63	W
Operating and storage temperature range	T_j, T_{stg}	– 55 … + 150	℃

Thermal resistance, chip-ambient (without heat sink)	R_{thJA}	≤ 200	K/W
DIN humidity category, DIN 40 040	–	E	–
IEC climatic category, DIN IEC 68-1	–	55/150/56	

Electrical Characteristics

at T_j = 25 °C, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage V_{GS} = 0, I_D = – 0.25 mA	$V_{(BR)DSS}$	– 50	–	–	V
Gate threshold voltage V_{GS} = V_{DS}, I_D = – 1 mA	$V_{GS(th)}$	– 0.8	– 1.5	– 2.0	
Zero gate voltage drain current V_{DS} = – 50 V, V_{GS} = 0 T_j = 25 °C T_j = 125 °C V_{DS} = – 25 V, V_{GS} = 0 T_j = 25 °C	I_{DSS}	 – – –	 – 0.1 – 2 –	 – 1.0 – 60 – 0.1	µA
Gate-source leakage current V_{GS} = – 20 V, V_{DS} = 0	I_{GSS}	–	– 1	– 10	nA
Drain-source on-resistance V_{GS} = – 10 V, I_D = – 0.17 A	$R_{DS(on)}$	–	5.3	10	Ω
Dynamic Characteristics					
Forward transconductance $V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$, I_D = – 0.17 A	g_{fs}	0.05	0.09	–	S
Input capacitance V_{GS} = 0, V_{DS} = – 25 V, f = 1 MHz	C_{iss}	–	30	40	pF
Output capacitance V_{GS} = 0, V_{DS} = – 25 V, f = 1 MHz	C_{oss}	–	17	25	
Reverse transfer capacitance V_{GS} = 0, V_{DS} = – 25 V, f = 1 MHz	C_{rss}	–	8	12	
Turn-on time t_{on}, (t_{on} = $t_{d(on)}$ + t_r) V_{DD} = – 30 V, V_{GS} = – 10 V, R_{GS} = 50 Ω, I_D = – 0.27 A	$t_{d(on)}$	–	7	10	ns
	t_r	–	12	18	
Turn-off time t_{off}, (t_{off} = $t_{d(off)}$ + t_f) V_{DD} = – 30 V, V_{GS} = – 10 V, R_{GS} = 50 Ω, I_D = – 0.27 A	$t_{d(off)}$	–	10	13	
	t_f	–	20	27	

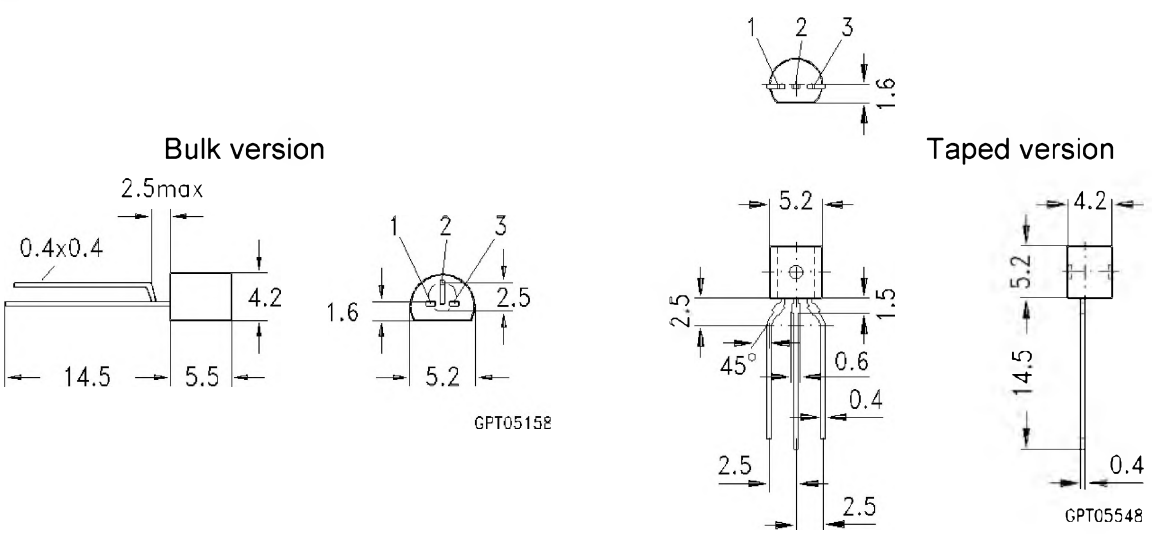
Electrical Characteristics (cont'd)

at T_j = 25 °C, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Reverse Diode					
Continuous reverse drain current T_A = 25 °C	I_S	–	–	– 0.17	A
Pulsed reverse drain current T_A = 25 °C	I_{SM}	–	–	– 0.68	
Diode forward on-voltage I_F = – 0.34 A, V_{GS} = 0	V_{SD}	–	0.95	– 1.2	V

Package Outline

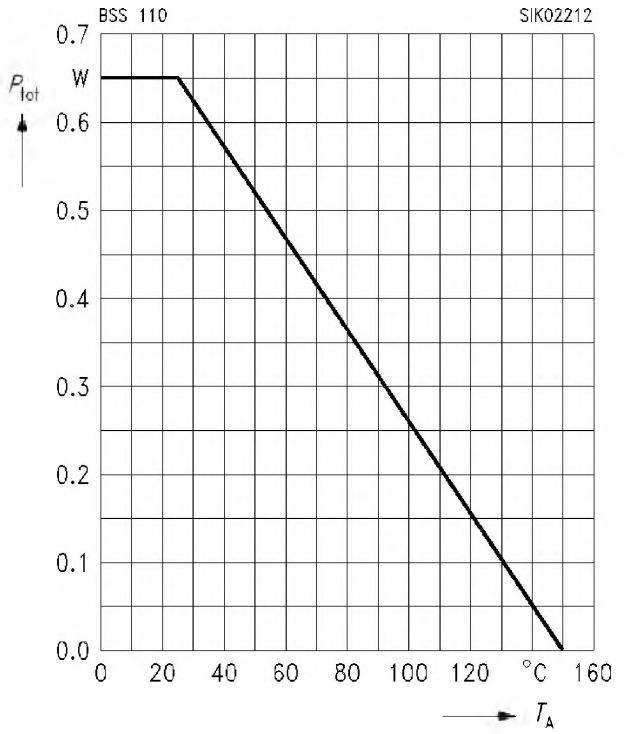
TO-92



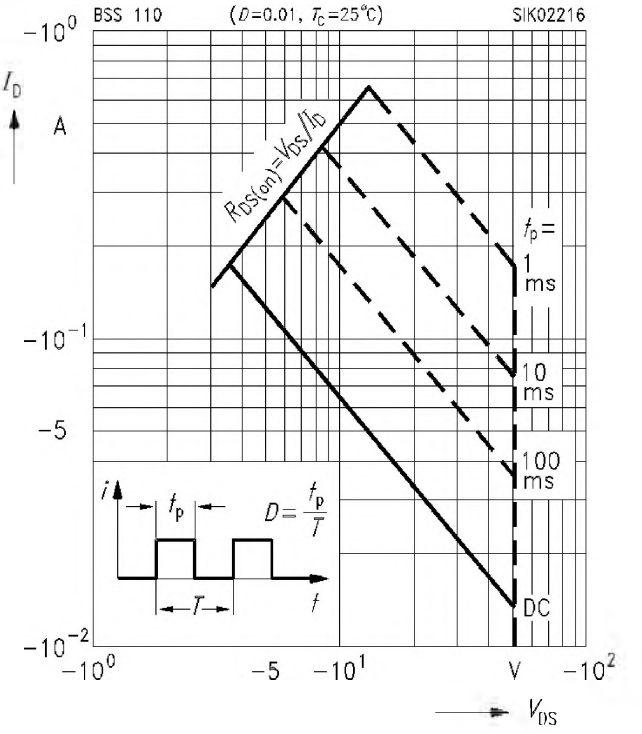
Dimensions in mm

Characteristics
at T_j = 25 °C, unless otherwise specified.

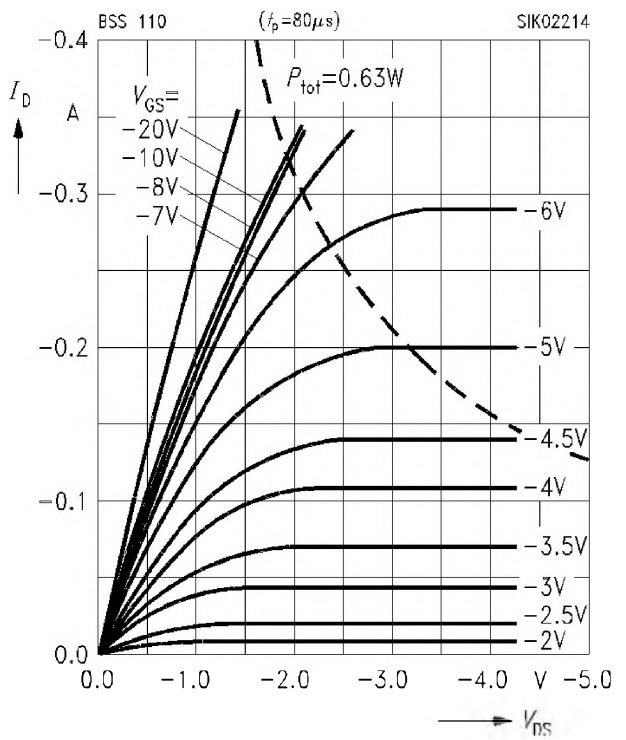
Total power dissipation $P_{tot} = f(T_A)$



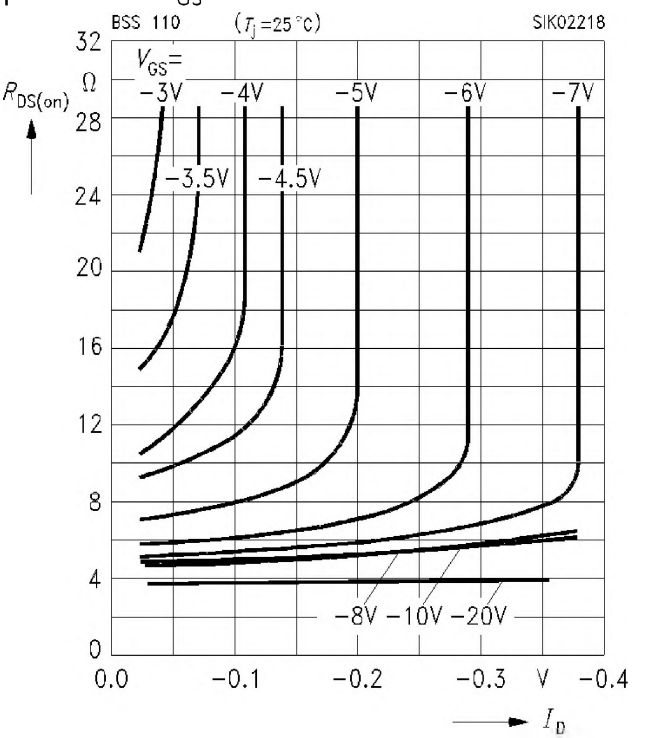
Safe operating area $I_D = f(V_{DS})$
parameter: D = 0.01, T_C = 25 °C



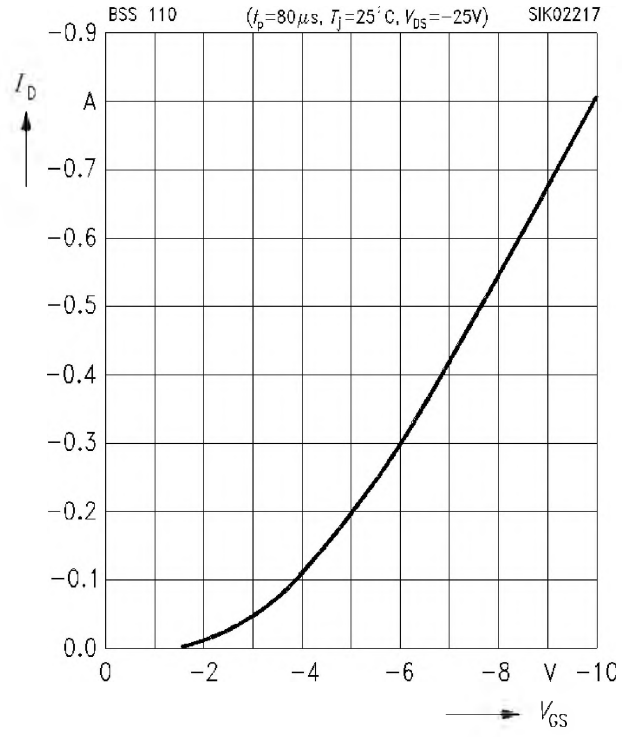
Typ. output characteristics $I_D = f(V_{DS})$
parameter: t_p = 80 µs



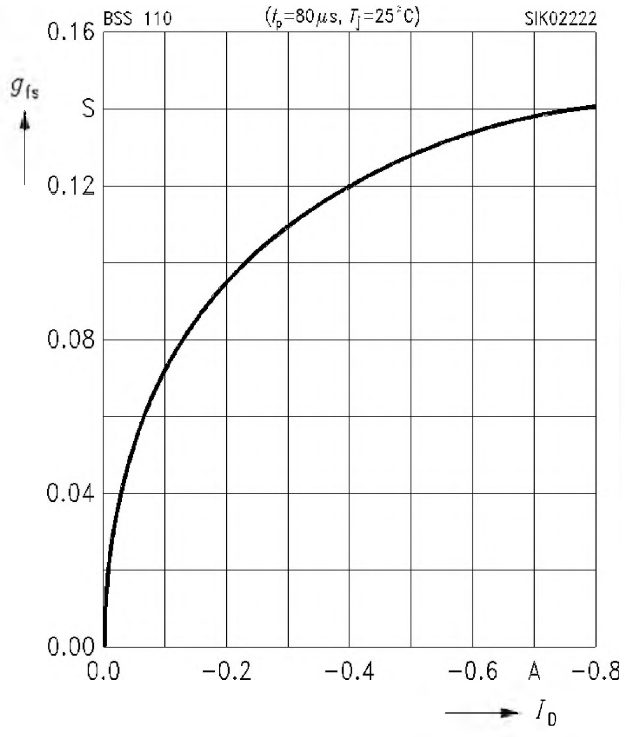
Typ. drain-source on-resistance
$R_{DS(on)} = f(I_D)$
parameter: V_{GS}



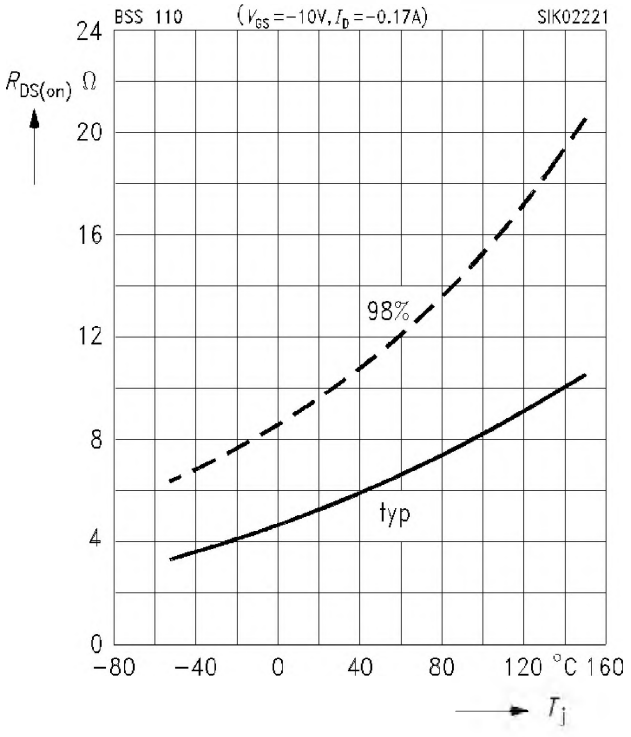
Typ. transfer characteristics $I_D = f(V_{GS})$
parameter: t_p = 80 µs, $V_{DS} \geq 2 \times I_D \times R_{DS(on)max.}$



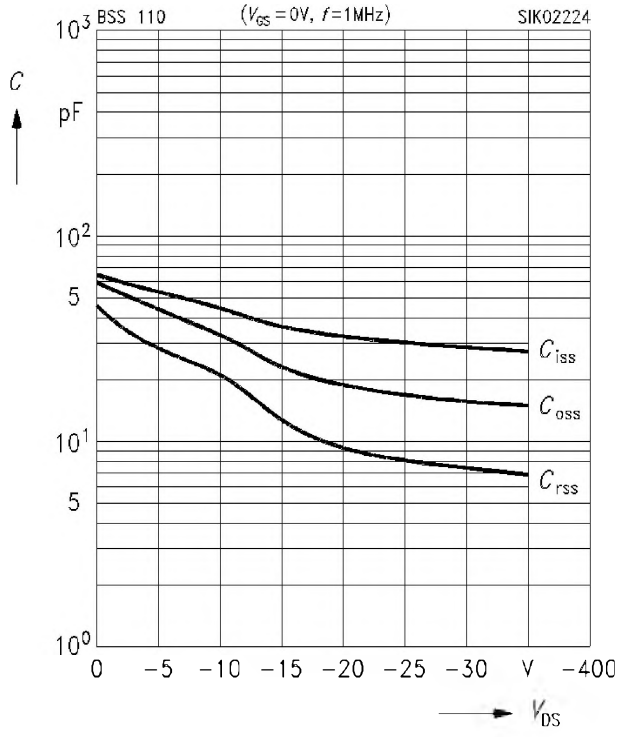
Typ. forward transconductance $g_{fs} = f(I_D)$
parameter: $V_{DS} \geq 2 \times I_D \times R_{DS(on)max.}$, t_p = 80 µs



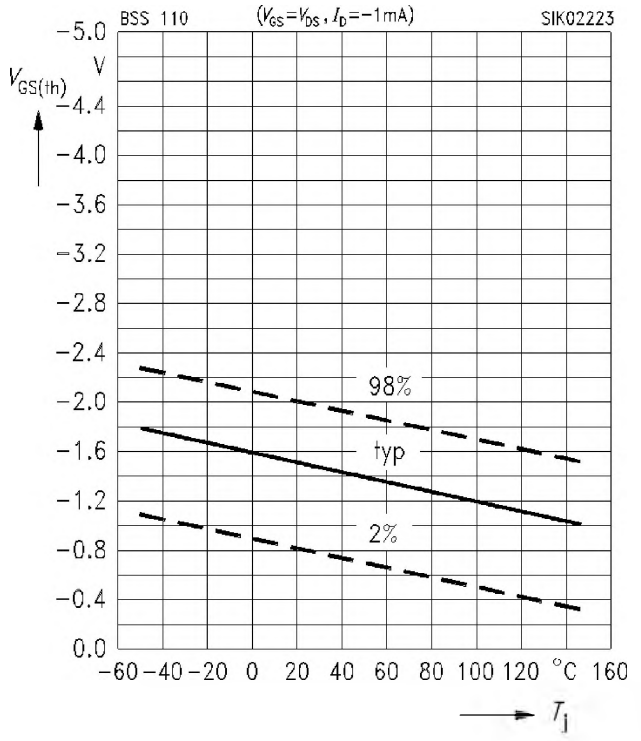
Drain-source on-resistance
$R_{DS(on)} = f(T_j)$
parameter: I_D = – 0.17 A, V_{GS} = – 10 V, (spread)



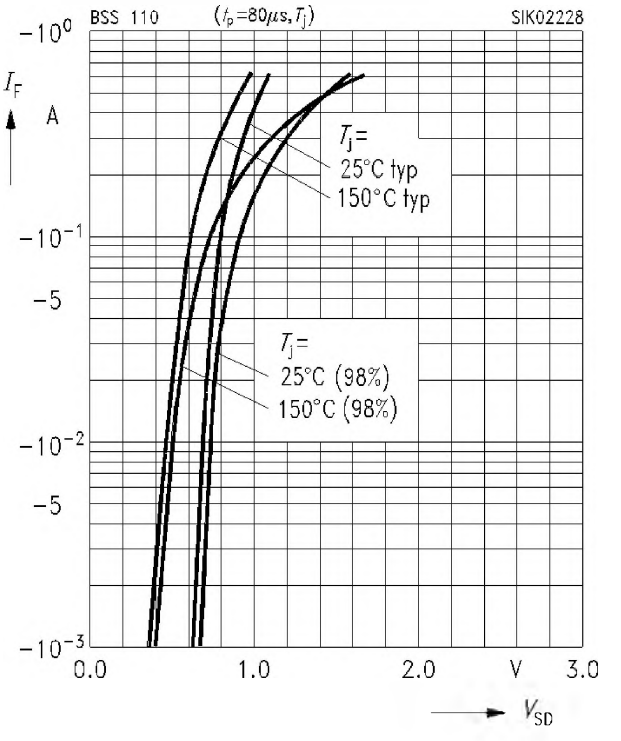
Typ. capacitances $C = f(V_{DS})$
parameter: V_{GS} = 0, f = 1 MHz



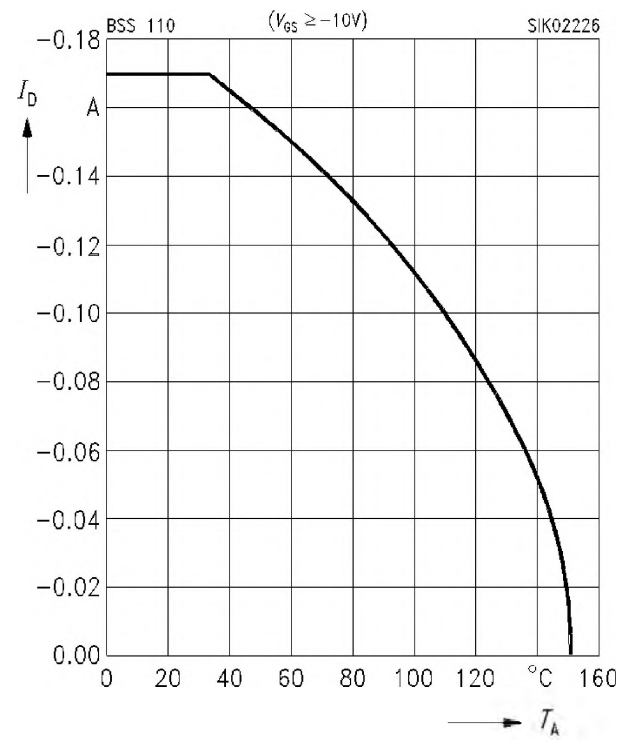
Gate threshold voltage $V_{GS(th)} = f(T_j)$
parameter: $V_{DS} = V_{GS}$, $I_D = -1$ mA, (spread)



Forward characteristics of reverse diode
$I_F = f(V_{SD})$
parameter: $t_p = 80$ µs, T_j, (spread)



Drain current $I_D = f(T_A)$
parameter: $V_{GS} \geq -10$ V



Drain-source breakdown voltage
$V_{(BR)\,DSS} = b \times V_{(BR)DSS}$ (25 °C)